

ECE1388 VLSI Design Methodology

Lecture 11: Circuit Families

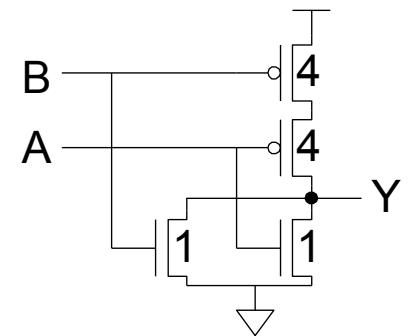
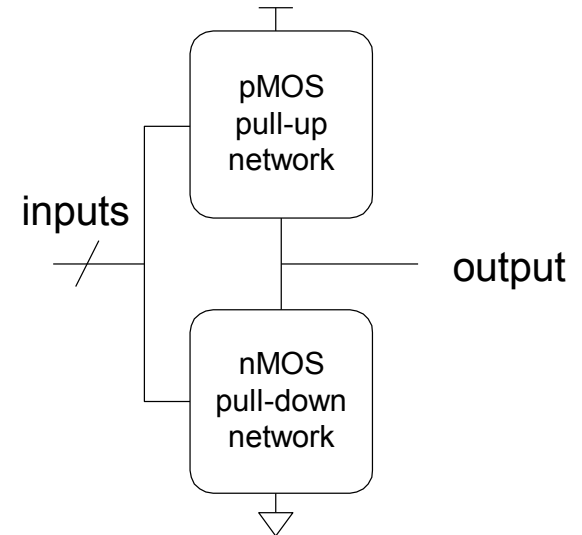
Outline

- ❑ Previously in the course
 - Static CMOS

- ❑ Today
 - Pseudo-nMOS Logic
 - Dynamic Logic
 - Pass Transistor Logic

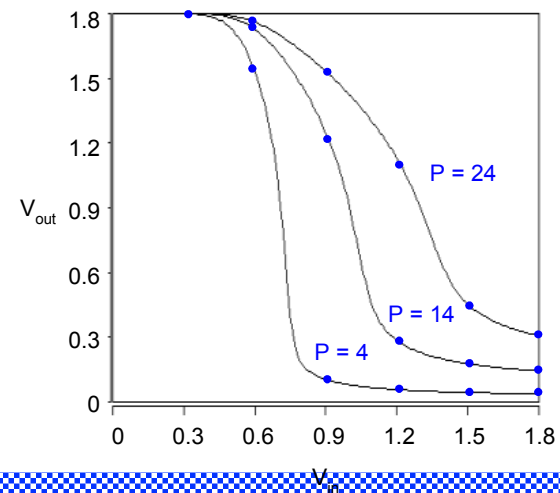
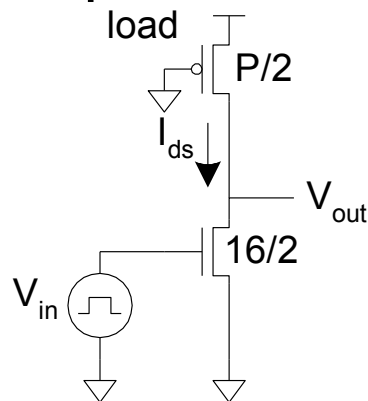
Introduction

- ❑ What makes a circuit fast?
 - $I = C \, dV/dt \rightarrow t_{pd} \propto (C/I) \Delta V$
 - low capacitance
 - high current
 - small swing
- ❑ Logical effort is proportional to C/I
- ❑ pMOS are the enemy!
 - High capacitance for a given current
- ❑ Can we remove the pMOS capacitance?
- ❑ Various circuit families try to do this...



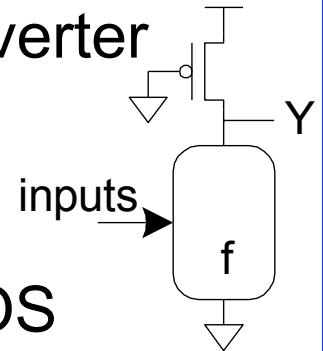
Pseudo-nMOS

- ❑ In the old days, nMOS processes had no pMOS
 - Instead, use pull-up transistor that is always ON
- ❑ In CMOS, use a pMOS that is always ON
 - *Ratio* issue: make pMOS about 1/4 effective strength of pulldown network ($\mu=2 \rightarrow 1/2$ nMOS eff. width: $P=8$)
 - Compromise: NM vs speed

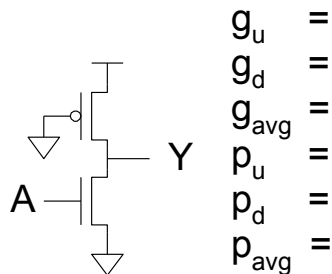


Pseudo-nMOS Gates

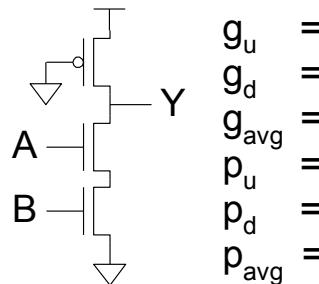
- ❑ Design for output current to match with unit inverter
 - nMOS fights pMOS: $I_d - I_u = 1$
- ❑ PMOS should be weak (typically 1/6 to 2/3)
 - $W_p = 1/2 W_n$ for 1/4 effective strength of NMOS



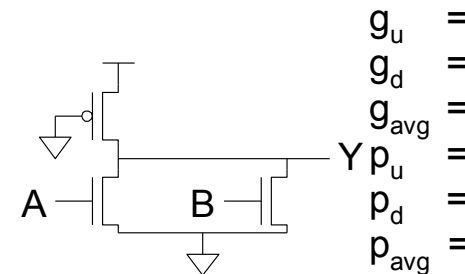
Inverter



NAND2

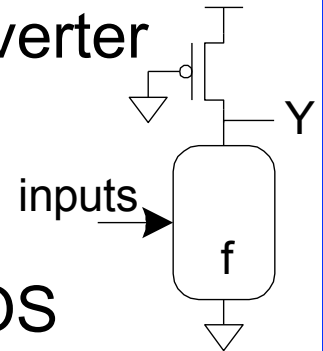


NOR2

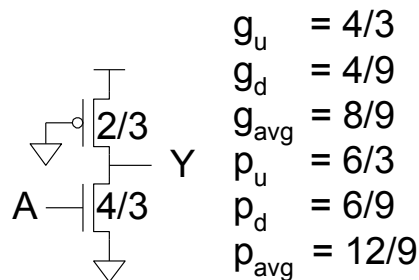


Pseudo-nMOS Gates

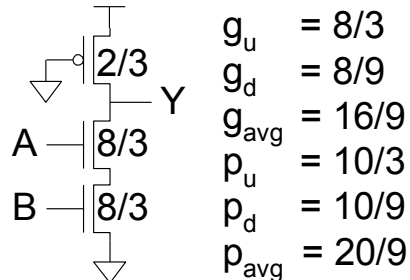
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 - $W_p = 1/2 W_n$ for 1/4 effective strength of NMOS
- ❑ Inv: $g_u = (4/3) / C_{in \text{ of inv equiv to pullup}} = (4/3) / (2/3 + 1/3) = 4/3$
- ❑ Inv: $I_u = I/3$; $I_d = 4I/3 - I/3 = I$ (as in unit inv) $\rightarrow g_d = (4/3)/3 = 4/9$



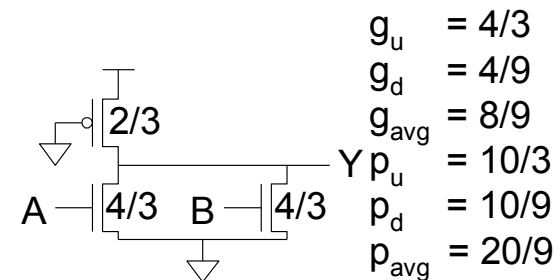
Inverter



NAND2



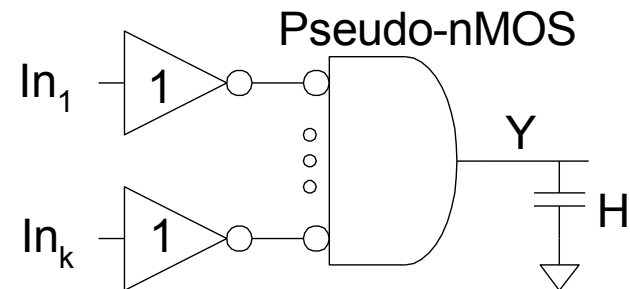
NOR2



Pseudo-nMOS Design

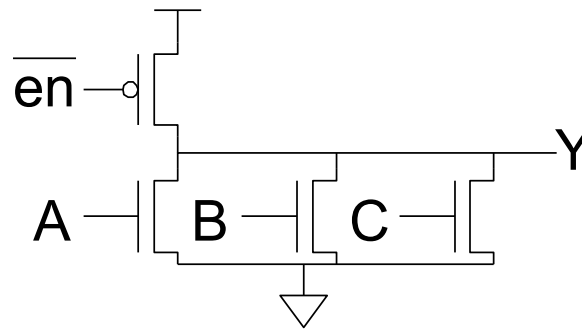
- ❑ Ex: Design a k-input AND gate using pseudo-nMOS. Estimate the delay driving a fanout of H

- ❑ $G = 1 * 8/9 = 8/9$
- ❑ $F = GBH = 8H/9$
- ❑ $P = 1 + (4+8k)/9 = (8k+13)/9$
- ❑ $N = 2$
- ❑ $D = NF^{1/N} + P = \frac{4\sqrt{2H}}{3} + \frac{8k+13}{9}$



Pseudo-nMOS Power

- ❑ Pseudo-nMOS draws power whenever $Y = 0$
 - Called static power $P = I_{DD} V_{DD}$
 - A few mA / gate * 1M gates would be a problem
 - Explains why nMOS went extinct
- ❑ Use pseudo-nMOS sparingly for wide NORs
- ❑ Turn off pMOS when not in use



Ratio Logic Power Example

- ❑ The chip contains a 32 word x 48 bit ROM
 - Uses pseudo-nMOS decoder and bitline pullups
 - On average, one wordline and 24 bitlines are high
- ❑ Find static power drawn by the ROM
 - $I_{\text{on-p}} = 36 \mu\text{A}$, $V_{\text{DD}} = 1.0 \text{ V}$

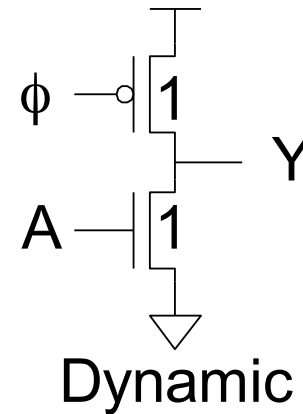
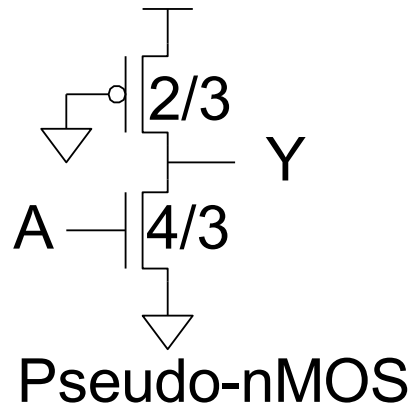
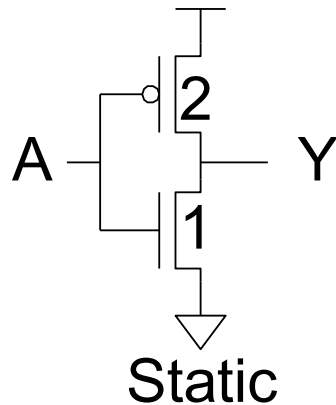
❑ Solution:

$$P_{\text{pull-up}} = V_{\text{DD}} I_{\text{pull-up}} = 36 \mu\text{W}$$

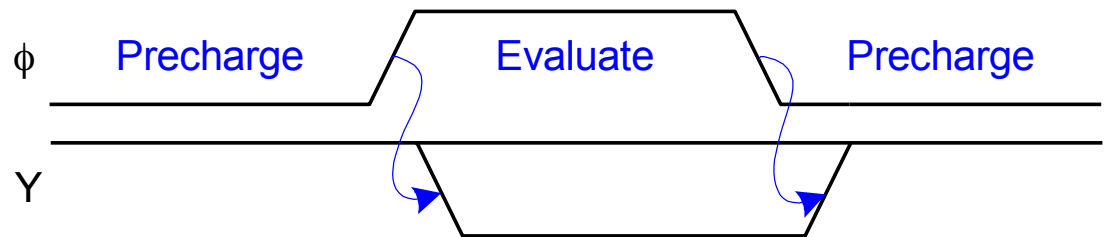
$$P_{\text{static}} = (31 + 24) P_{\text{pull-up}} = 1.98 \text{ mW}$$

Dynamic Logic

- ❑ *Dynamic* gates uses a clocked pMOS pullup
- ❑ Two modes: *precharge* and *evaluate*

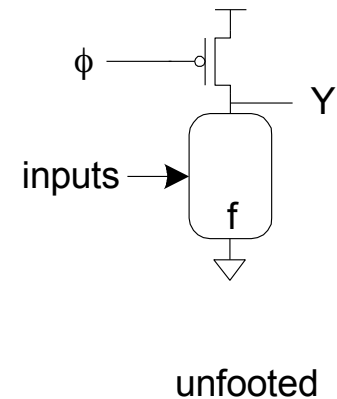
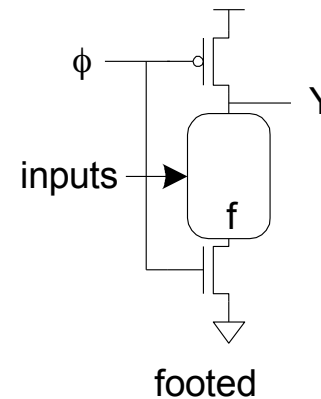
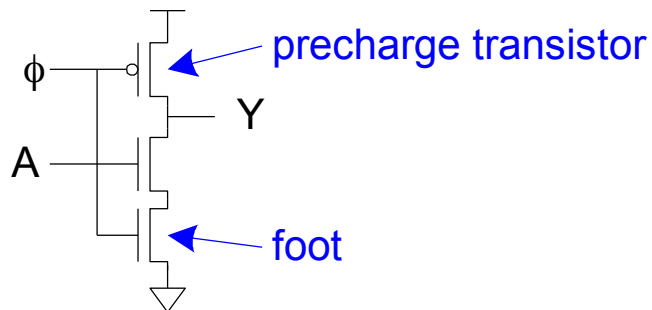


Pulldown network must be OFF during precharge phase



The Foot

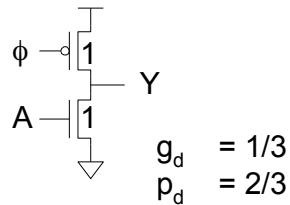
- ❑ What if pulldown network is ON during precharge?
- ❑ Use series evaluation transistor (**foot**) to prevent fight



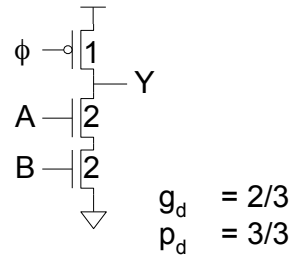
Logical Effort

unfooted

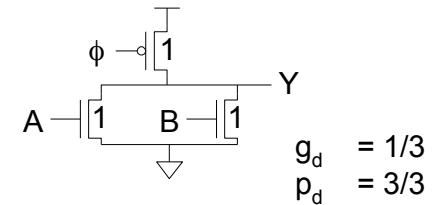
Inverter



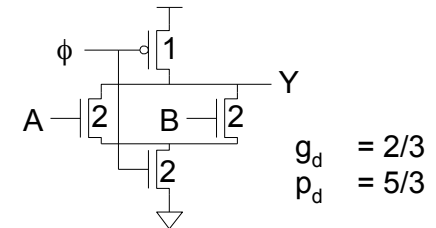
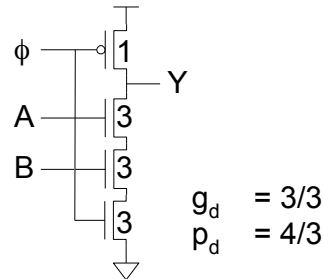
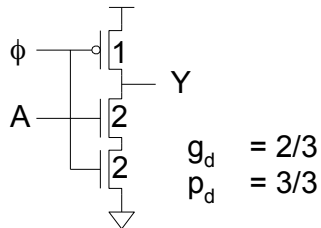
NAND2



NOR2

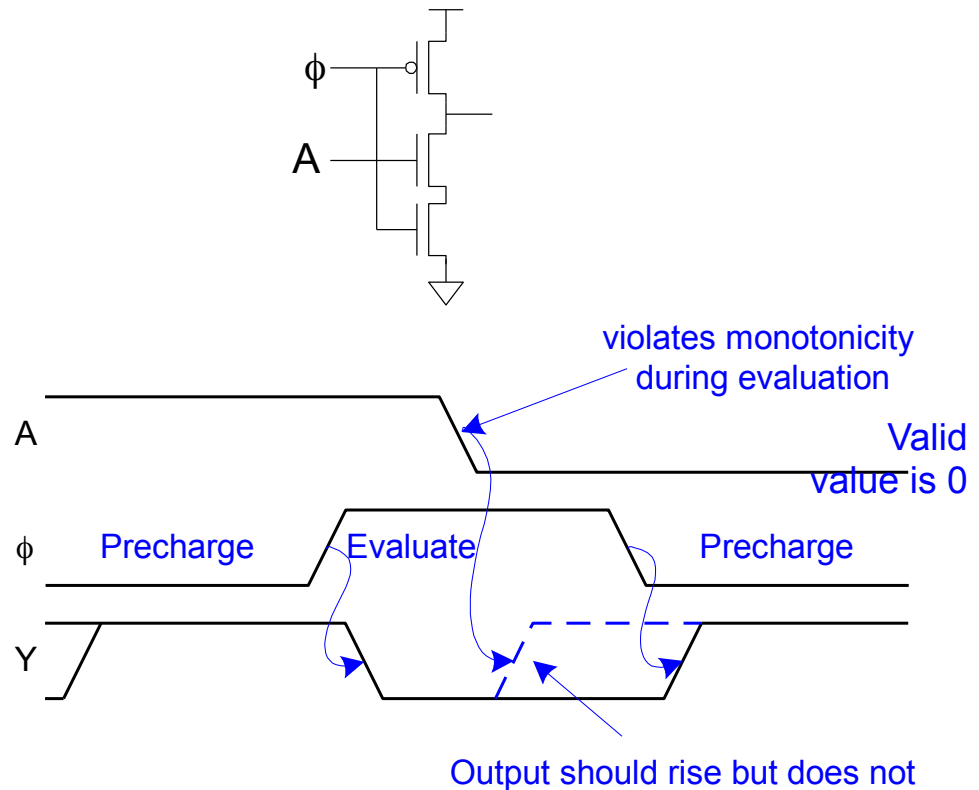


footed



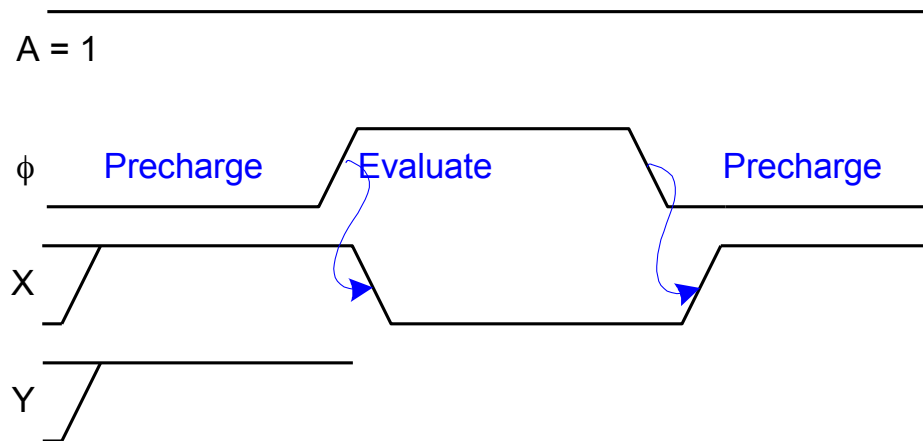
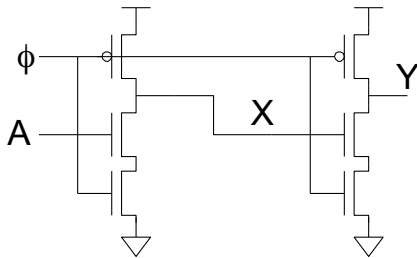
Monotonicity

- ❑ Dynamic gates require *monotonically rising* inputs during evaluation
 - 0 \rightarrow 0
 - 0 \rightarrow 1
 - 1 \rightarrow 1
 - But not 1 \rightarrow 0



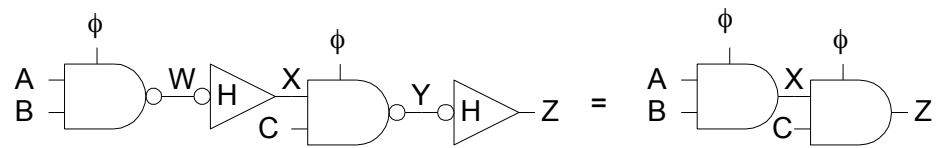
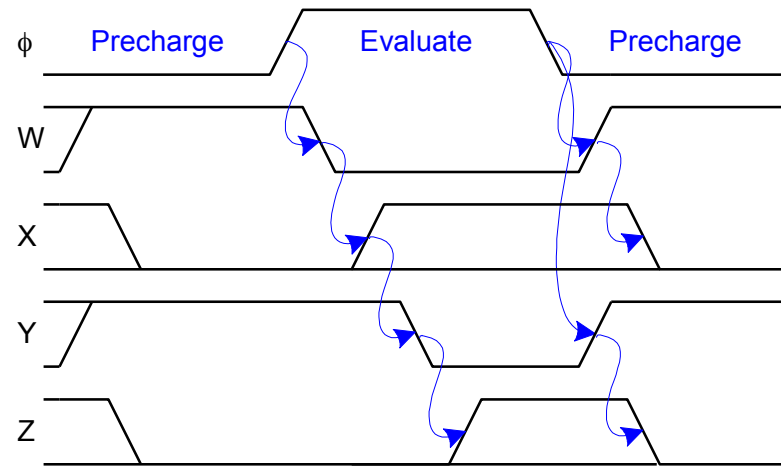
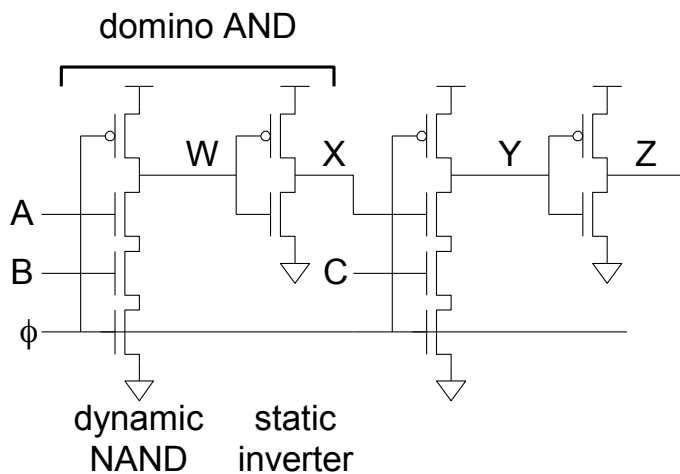
Monotonicity Woes

- ❑ But dynamic gates produce monotonically falling outputs during evaluation
- ❑ Illegal for one dynamic gate to drive another!



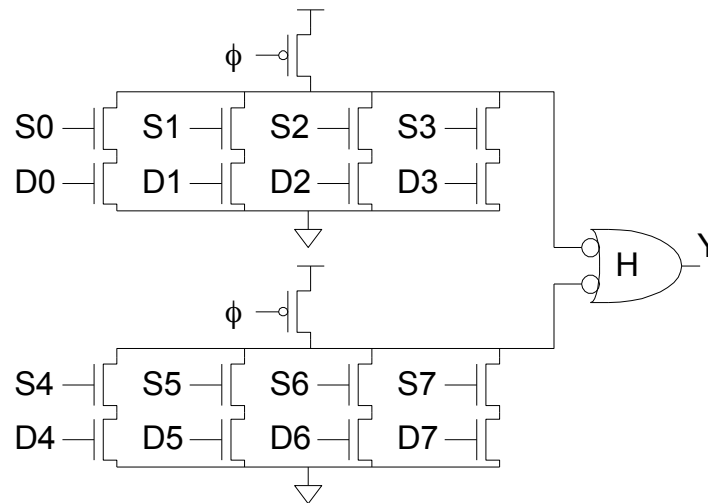
Domino Gates

- ❑ Follow dynamic stage with inverting static gate
 - Dynamic / static pair is called domino gate
 - Produces monotonic outputs



Domino Optimizations

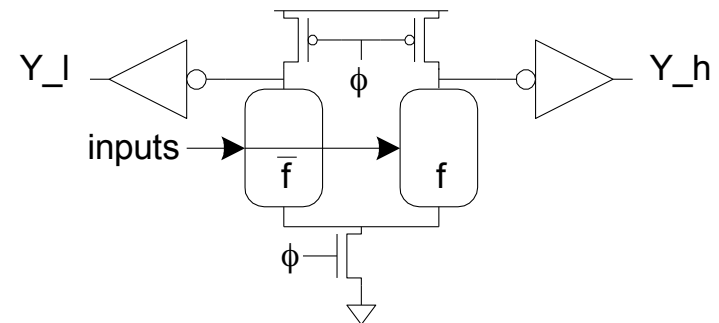
- ❑ Each domino gate triggers next one, like a string of dominos toppling over
- ❑ Gates evaluate sequentially but precharge in parallel
- ❑ Thus evaluation is more critical than precharge
- ❑ HI-skewed static stages can perform logic



Dual-Rail Domino

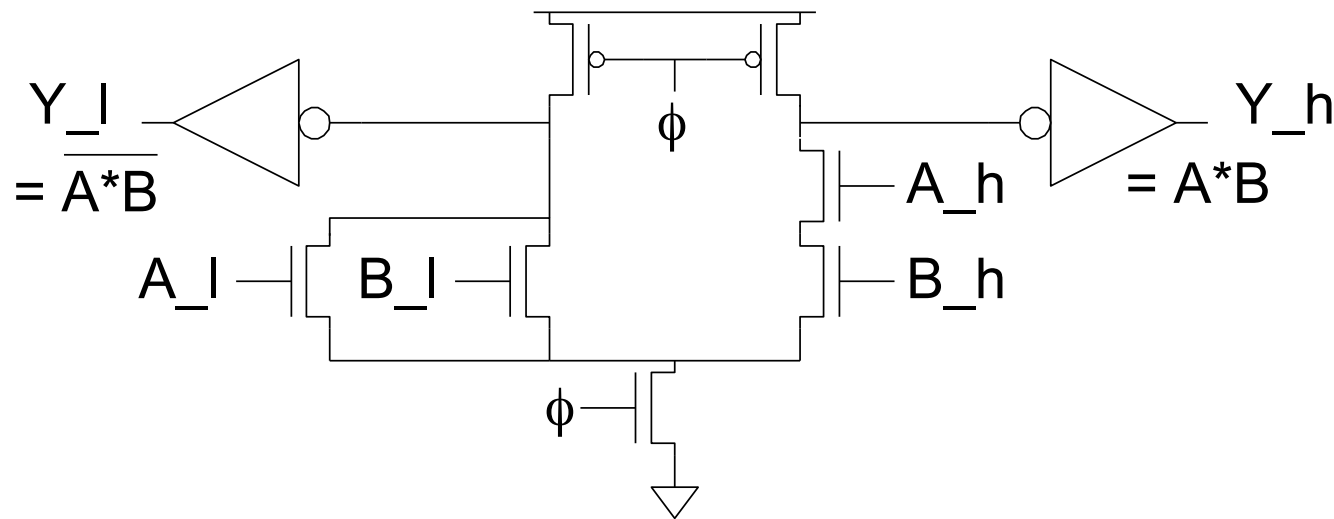
- ❑ Domino only performs noninverting functions:
 - AND, OR but not NAND, NOR, or XOR
- ❑ Dual-rail domino solves this problem
 - Takes true and complementary inputs
 - Produces true and complementary outputs

sig_h	sig_l	Meaning
0	0	Precharged
0	1	'0'
1	0	'1'
1	1	invalid



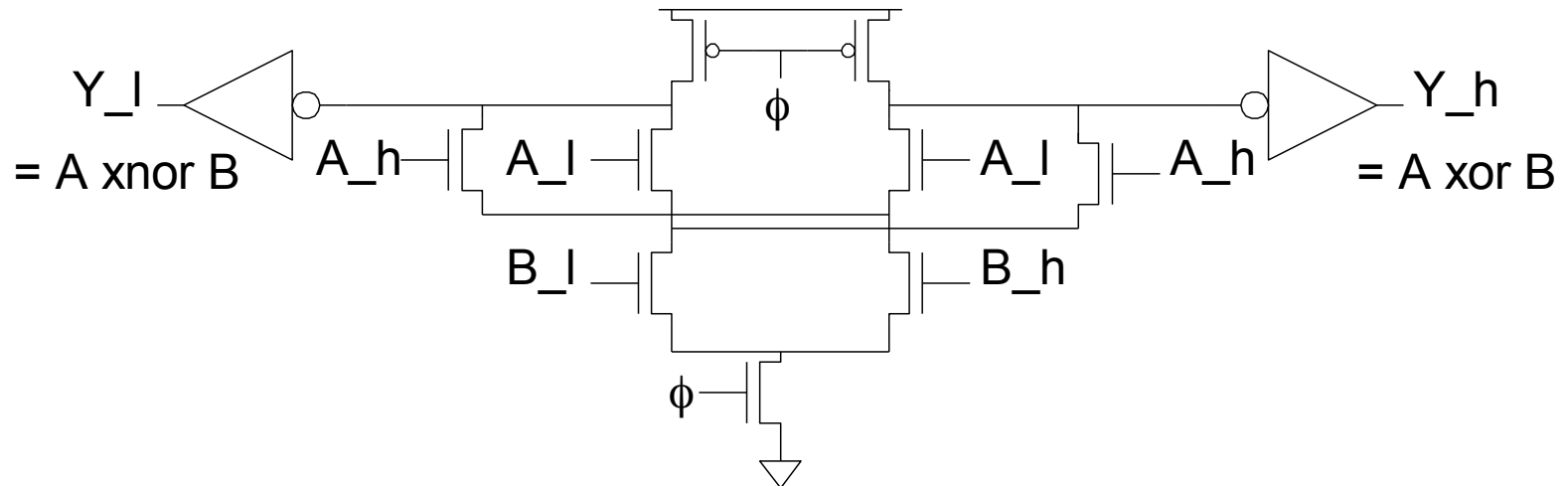
Example: AND/NAND

- ❑ Given A_h, A_l, B_h, B_l
- ❑ Compute $Y_h = AB, Y_l = \overline{AB}$
- ❑ Pulldown networks are conduction complements



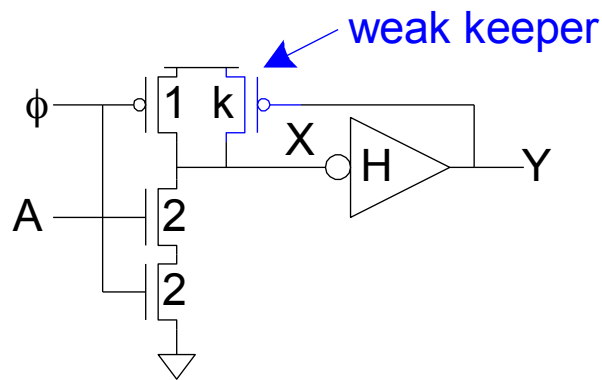
Example: XOR/XNOR

- Sometimes possible to share transistors



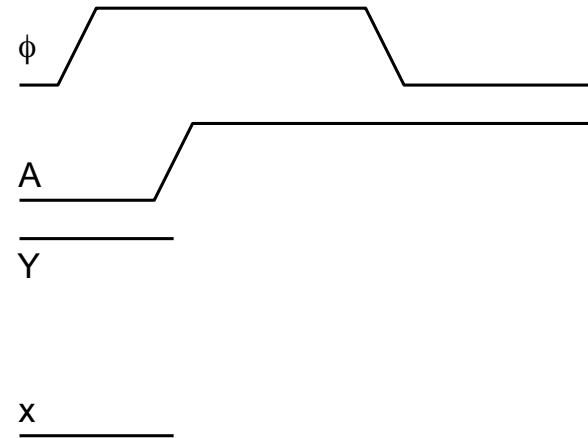
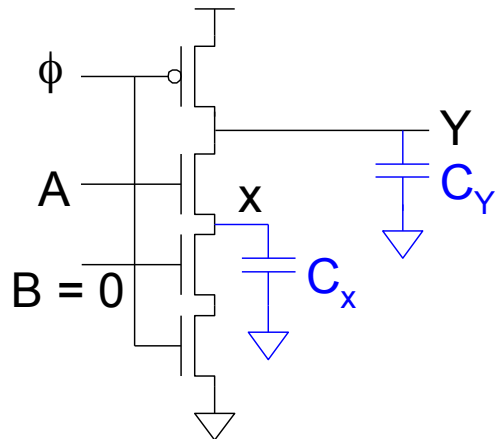
Leakage

- ❑ Dynamic node floats high during evaluation
 - Transistors are leaky ($I_{\text{OFF}} \neq 0$)
 - Dynamic value will leak away over time
 - Formerly milliseconds, now nanoseconds
- ❑ Use keeper to hold dynamic node
 - Must be weak enough not to fight evaluation



Charge Sharing

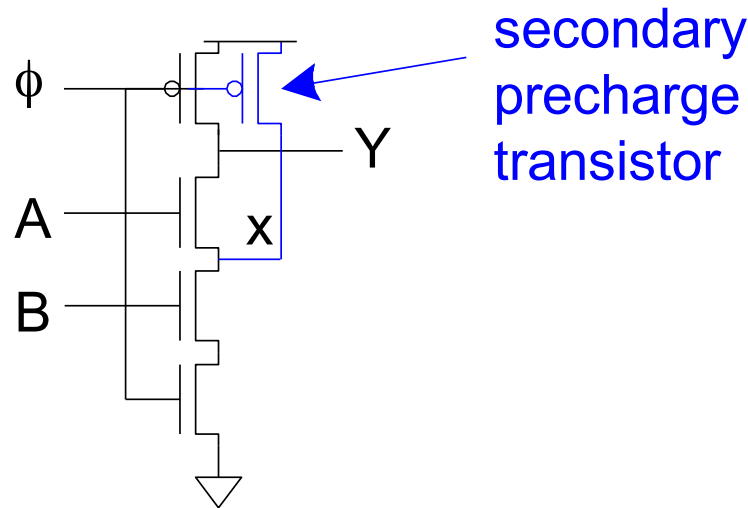
- ❑ Dynamic gates suffer from charge sharing



$$V_x = V_Y = \frac{C_Y}{C_x + C_Y} V_{DD}$$

Secondary Precharge

- ❑ Solution: add secondary precharge transistors
 - Typically need to precharge every other node
- ❑ Big load capacitance C_Y helps as well



Noise Sensitivity

- ❑ Dynamic gates are very sensitive to noise
 - Inputs: $V_{IH} \approx V_{tn}$
 - Outputs: floating output susceptible noise
- ❑ Noise sources
 - Capacitive crosstalk
 - Charge sharing
 - Power supply noise
 - Feedthrough noise
 - And more!

Power

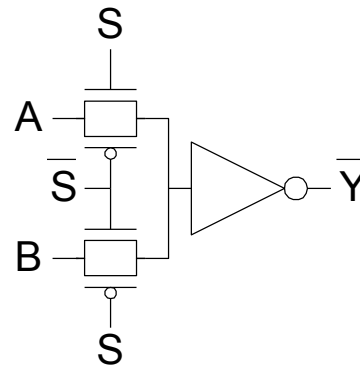
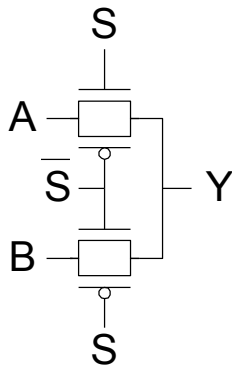
- ❑ Domino gates have high activity factors
 - Output evaluates and precharges
 - If output probability = 0.5, $\alpha = 0.5$
 - Output rises and falls on half the cycles
 - Clocked transistors have $\alpha = 1$
- ❑ Leads to very high power consumption

Domino Summary

- ❑ Domino logic is attractive for high-speed circuits
 - 1.3 – 2x faster than static CMOS
 - But many challenges:
 - Monotonicity, leakage, charge sharing, noise
- ❑ Widely used in high-performance microprocessors in 1990s when speed was king
- ❑ Largely displaced by static CMOS now that power is the limiter
- ❑ Still used in memories for area efficiency

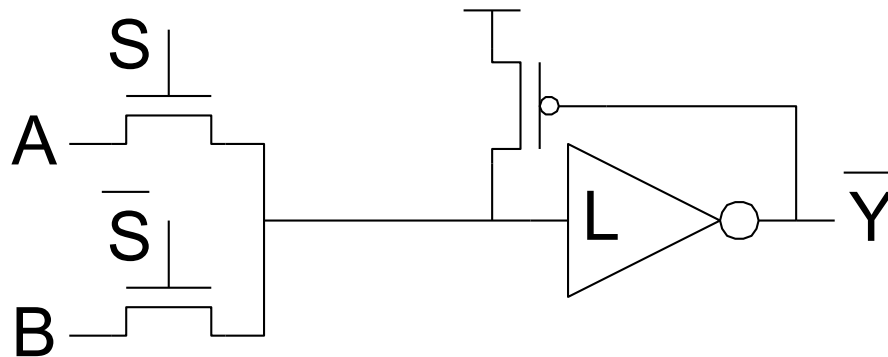
Pass Transistor Circuits

- ❑ Use pass transistors like switches to do logic
- ❑ Inputs drive diffusion terminals as well as gates
- ❑ CMOS + Transmission Gates:
 - 2-input multiplexer
 - Gates should be restoring



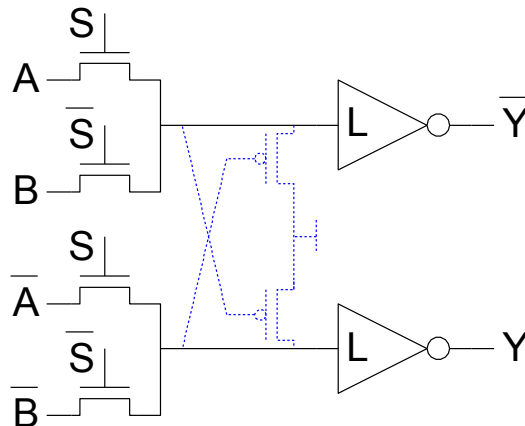
LEAP

- ❑ **LEA**n integration with **P**ass transistors
- ❑ Get rid of pMOS transistors
 - Use weak pMOS feedback to pull fully high
 - Ratio constraint



CPL

- ❑ Complementary Pass-transistor Logic
 - Dual-rail form of pass transistor logic
 - Avoids need for ratioed feedback
 - Optional cross-coupling for rail-to-rail swing



Pass Transistor Summary

- ❑ Researchers investigated pass transistor logic for general purpose applications in the 1990' s
 - Benefits over static CMOS were small or negative
 - No longer generally used
- ❑ However, pass transistors still have a niche in special circuits such as memories where they offer small size and the threshold drops can be managed